

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6126	438/257,258,241,275,689.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/28 12:15
L2	0	1 and ((thin film stack) with \$5mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 12:22
L3	9	1 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 12:23

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	(thin film stack) same hardmask same ((anti reflective coating) or ARC) same etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:38
S2	0	(thin film stack) same hardmask same ((anti reflective coating) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:17
S3	0	((thin film stack) same hardmask) and ((anti reflective coating) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:22
S4	0	((thin film stack) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:18
S5	916	(thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:31
S6	7	(thin film stack) and hardmask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:19
S7	435233	(anti reflective coating) or ARC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:33
S8	364	S7 and hardmask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:23
S9	350	S8 and etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:24

## EAST Search History

S10	345	S9 and method	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:28
S11	111	S9 and apparatus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:29
S12	34	(thin film stack) with apparatus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:32
S13	0	(thin film stack) with apparatus with ARC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:32
S14	23816	((anti reflective coating) or ARC) with apparatus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:34
S15	127	((anti reflective coating) or ARC) with apparatus with (thin film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:36
S16	1525985	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:35
S17	28	S16 and S15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:35
S18	1	S16 and ((anti reflective coating) with apparatus with (thin film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:37
S19	10	apparatus same hardmask same ((anti reflective coating) or ARC) same etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:39

## EAST Search History

S20	0	apparatus same hardmask same (anti reflective coating) same etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:40
S21	34	apparatus with (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:41
S22	18	S16 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:44
S23	2424	S16 and (antireflection coating)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 12:45
S24	55	S16 and ((antireflection coating) with apparatus)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 13:00
S25	267	S16 and ((antireflection coating) with method)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 13:01
S26	48	S16 and ((antireflection coating) with method with etch\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 14:59
S27	342	"16" and ((antireflection coating) with method)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 15:05
S28	3	S27 and chalcogenide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/06/13 15:05

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3	("4142926").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/26 14:43
S2	12667	semiconductor with lithography	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 14:46
S3	24	S2 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:47
S4	1543042	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 14:28
S5	43735	S4 and lithography	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 14:46
S6	93	S5 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:47
S7	0	S5 and ((thin film stack) with polysilicon with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:48
S8	0	S5 and ((thin film stack) same polysilicon same oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:49
S9	10	S5 and ((thin film stack) and polysilicon and oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:57

## EAST Search History

S10	4	S9 and ((anti reflectie) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:58
S11	4	S10 and \$5mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:58
S12	71	S4 and ((thin film stack) and polysilicon and oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:57
S13	15	S12 and ((anti reflectie) or ARC) and \$5mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 15:00
S14	15	S13 and etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:59
S15	4	S14 and (((anti reflectie) or ARC) with pattern)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:02
S16	0	S4 and (((anti reflectie) or ARC) with pattern with hardmask) and ((thin film stack) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:05
S17	0	S4 and (((anti reflectie) or ARC) same pattern same hardmask) and ((thin film stack) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:06
S18	0	S4 and (((anti reflectie) or ARC) same pattern same hardmask) and ((thin film stack) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:08
S19	0	S4 and (((anti reflectie) or ARC) same hardmask) and ((thin film stack) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:07

## EAST Search History

S20	160	S4 and (((anti reflectie) or ARC) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:07
S21	130	S4 and (((anti reflectie) or ARC) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:07
S22	64	S4 and (((anti reflectie) or ARC) same pattern same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:08
S23	0	S4 and (((anti reflectie) or ARC) same pattern same hardmask) and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:09
S24	445	S4 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:11
S25	0	S4 and ((thin film stack) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:11
S26	10	S4 and ((thin film stack) with \$5mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/11/09 14:28
S27	1584605	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 14:28
S28	11	S27 and ((thin film stack) with \$5mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/11/09 14:29
S29	2	("20050098821").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 14:30

## EAST Search History

S30	2	S29 and hardmask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 14:43
S31	2	S29 and hardmask and (ARC (anti adj reflect\$4 adj coating))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 14:45



PALM Intranet

Application  
Number

SEARCH

IDS Flag Clearance for Application 10808793

IDS  
Information

Content	Mailroom Date	Entry Number	IDS Review	Reviewer
M844	03-24-2004	11	<input checked="" type="checkbox"/>	07-06-2004 14:43:35 jsmalls

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